Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1330	257/368.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:25
L2	0	(differential adj transistor adj pair) with (drain adj collector) with second with third with (gate adj base).clm.	US-PGPUB	OR	ON	2005/10/03 12:26
S1	4	("6335655"|"6345178").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:49
S2	8	(bipolar adj differential adj transistor adj pair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:06
S3	3983	(emitter with source) and (drain with collector) and (gate with base)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:51
S4	312	S3 and (common adj source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:29
S5	0	S4 and (drain with collector with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:16
S6	0	S4 and (drain/collector with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:52
S7	20	S4 and ((drain or collector) with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:30
S8	34	S3 and (drain with collector with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:17

S9	486	S3 and (differential with pair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:29
S10	392	S3 and (differential with transistor with pair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:33
S11	8	S10 and ((drain or collector) with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:38
S12	486	S3 and (differential with pair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:33
S13	18	S12 and ((drain or collector) with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:33
S14	1	S2 and edge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:38
S15	1937	(differential adj transistor adj pair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:38
S16	306	S15 and edge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:41
S17	11	S15 and ((drain or collector) with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:39
S18	21	S15 and (edge with cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:41

S19	640	integrated adj bipolar	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:58
S20	70	S19 and differential and pair	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:54
S21	1	S20 and (cell with edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:50
S22	0	S20 and (first adj base) and (first adj collector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:54
S23	3	S19 and (first adj base) and (first adj collector) and (common with base) and (common with collector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 17:56
S24	691	integrated adj (MOSFET or FET or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:00
S25	13	S19 and S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:00
S26	4759	(transistor adj pair) and cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:07
S27	8	S26 and (cell with edge with (drain or collector))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:08